TOSHIBA Photocoupler Infrared LED + Photo IC

TLP550

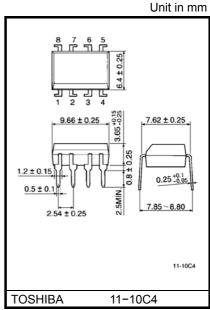
Degital Logic Isolation
Line Receiver Feedback Control
Power Supply Control
Switching Power Supply
Transistor Invertor

TLP550 constructs a high emitting diode and a one chip photo diodetransistor.

TLP550 has no base connection, and is suitable for application at noisy environmental condition.

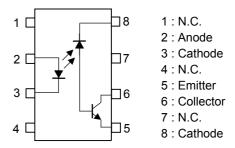
This unit is 8-lead DIP package.

- Isolation voltage: 2500 Vrms (min.)
- Switching speed: t_{pHL} , $t_{pLH} = 0.5\mu s$ (typ.)(RL=1.9 k Ω)
- TTL compatible
- UL recognized: UL1577, file No. E67349

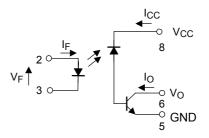


Weight: 0.54 g (typ.)

Pin Configuration (top view)



Schematic





Current Transfer Ratio

Classification		sfer Ratio (%) /IF)	Marking of Classificatio		
	MIN	MAX			
(None)	10	_	Blank, O, Y		
Rank O	19	_	0		
Rank Y	35	_	Υ		

Absolute maximum Ratings (Ta = 25°C)

	Characteristic		Symbol	Rating	Unit
ΓED	Forward current	(Note 1)	l _F	25	mA
	Pulse forward current	(Note 2)	I _{FP}	50	mA
	Peak transient forward current	(Note 3)	I _{FPT}	1	А
	Reverse voltage		V _R	5	V
	Diode power dissipation	(Note 4)	P_{D}	45	mW
Detector	Output current		ΙO	8	mA
	Peak output current		I _{OP}	16	mA
	Supply voltage		V _{CC}	-0.5~15	V
	Output voltage		Vo	-0.5~15	V
	Output power dissipation	(Note 5)	PO	100	mW
Оре	ating temperature range		T _{opr}	−55~100	°C
Sto	Storage temperature range			-55~125	°C
Lea	Lead solder temperature (10s)			260	°C
Isol (AC	Isolation voltage (AC, 1min., R.H. = 40~60%) (Note 6			2500	Vrms

⁽Note 1) Derate 0.8mA above 70°C.

⁽Note 2) 50% duty cycle, 1ms pulse width. Derate 1.6mA / °C above 70°C.

⁽Note 3) Pulse width 1µs, 300pps.

⁽Note 4) Derate 0.9mW / °C above 70°C.

⁽Note 5) Derate 2mW / $^{\circ}$ C above 70 $^{\circ}$ C.

Electrical Characteristics (Ta = 25°C)

Characteristic		Symbol	Test condition		Min.	Тур.	Max.	Unit	
	orward voltage V _F I _F = 16 mA				1.45	1.65	1.85	V	
CED	Forward voltage temperature coefficient	ΔV _F /ΔTa	I _F = 16 mA			ı	-2	1	mV / °C
	Reverse current	I _R	V _R = 5 V			I	_	10	μΑ
	Capacitance between terminal	C _T	V _F = 0, f = 1MHz			-	60	1	pF
Detector	High level output current	I _{OH (1)}	I _F = 0 mA, V _{CC} = V _O = 5.5 V			_	3	500	nA
		I _{OH} (2)	$I_F = 0 \text{ mA}, V_{CC} = V_O = 15 \text{ V}$			_	_	5	μΑ
		Іон	I _F = 0 mA, V _{CC} = V _O = 15 V Ta = 70°C			_	_	50	μΑ
	High level supply voltage	Іссн	I _F = 0 mA, V _{CC} = 15 V			_	0.01	1	μΑ
	Current transfer ratio	I _O / I _F	I _F = 16 mA V _{CC} = 4.5 V V _O = 0.4 V	Ta = 25°C		10	30	_	
Coupled					Rank: 0	19	30	_	%
					Rank : Y	35	50		
				Ta = 0~70°C		5	_	_	
					Rank: 0, Y	15	_	ı	
	Low level output voltage	V _{OL}	I_F = 16 mA, V_{CC} = 4.5 V I_O = 1.1 mA (rank 0: I_O = 2.4mA)		_	_	0.4	V	
	Isolation resistance	R _S	R.H. = 40~60%, V = 1kV DC (Note 6)			_	10 ¹²	_	Ω
	Capacitance between input to output	CS	V = 0, f = 1MHz			1	0.8	1	pF

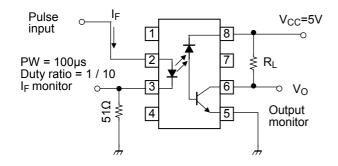
Switching Characteristics (Ta = 25°C)

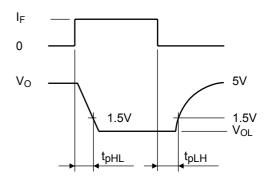
Characteristic	Symbol	Test Condition		Тур.	Max.	Unit
Propagation delay time	t _{pHL}	$I_F = 0 \rightarrow 16 \text{ mA}, V_{CC} = 5V, R_L = 4.1 \text{ k}\Omega$	_	0.3	0.8	116
(H→ L)		(Note 7) Rank 0: R _L = 1.9 kΩ	<u> </u>	0.5	0.8	μs
Propagation delay time	t _{pLH}	$I_F = 16 \rightarrow 0$ mA, $V_{CC} = 5V$, $R_L = 4.1$ kΩ		1.0	2.0	μs
(L→ H)		(Note 7) Rank 0: R _L = 1.9 kΩ	<u> </u>	0.6	1.2	μδ
Common mode transient immunity at high output level		I_F = 0 mA, V_{CM} = 200 V_{p-p} R_L = 4.1 kΩ (rank 0: R_L = 1.9 kΩ) (Note	— 8)	1500	ı	V /µs
Common mode transient immunity at low output level	C _{ML}	I_F = 16 mA, V_{CM} = 200 V_{p-p} R_L = 4.1 kΩ (rank 0: R_L = 1.9 kΩ) (Note	8)	-1500	_	V /µs

(Note 6) Device considered two-terminal device: Pins 1, 2, 3 and 4 shorted together and pin 5, 6, 7 and 8 shorted together.

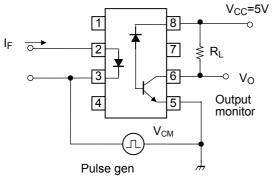
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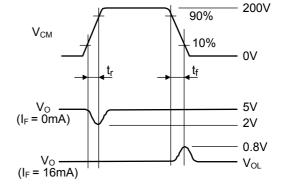
(Note 7) Switching time test circuit.





(Note 8) Common mode transient immunity test circuit.

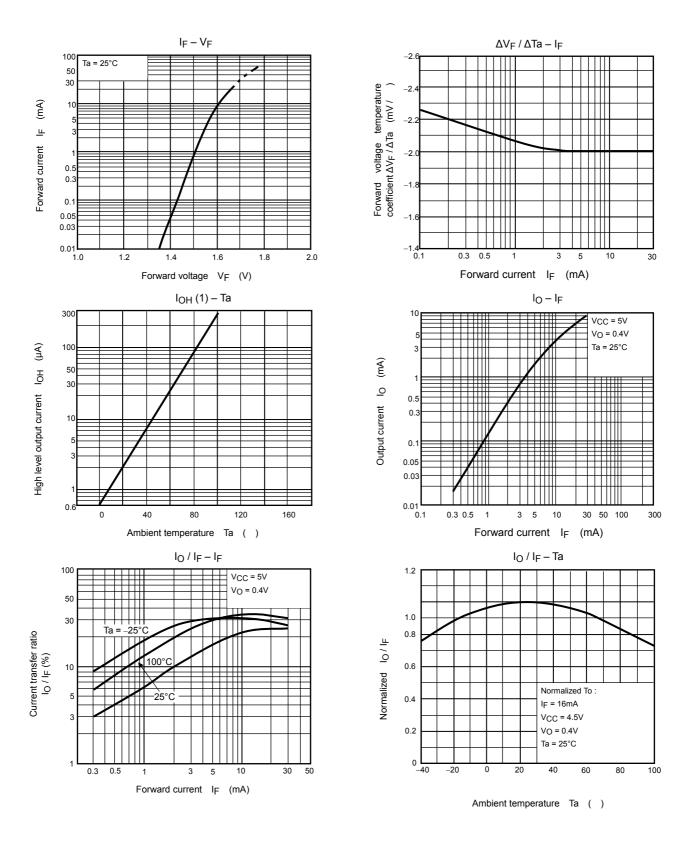


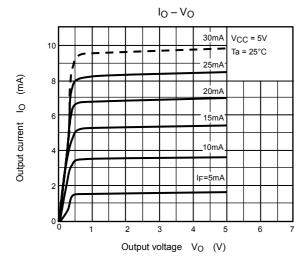


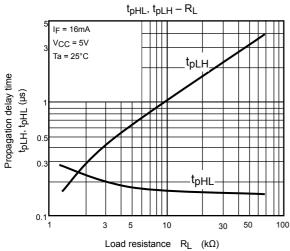
$$Z_{O} = 50\Omega$$

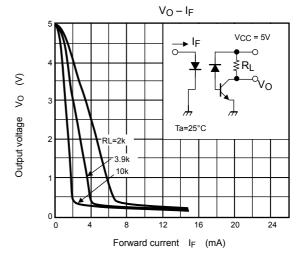
$$CM_{H} = \frac{160 \text{ (V)}}{t_{f} \text{ (µs)}} \quad , \quad CM_{L} = \frac{160 \text{ (V)}}{t_{f} \text{ (µs)}}$$

(Note 9) Maximum electrostatic discharge voltage for any pins: 100V (C = 200pF, R = 0)









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